2SD1257, 2SD1257A

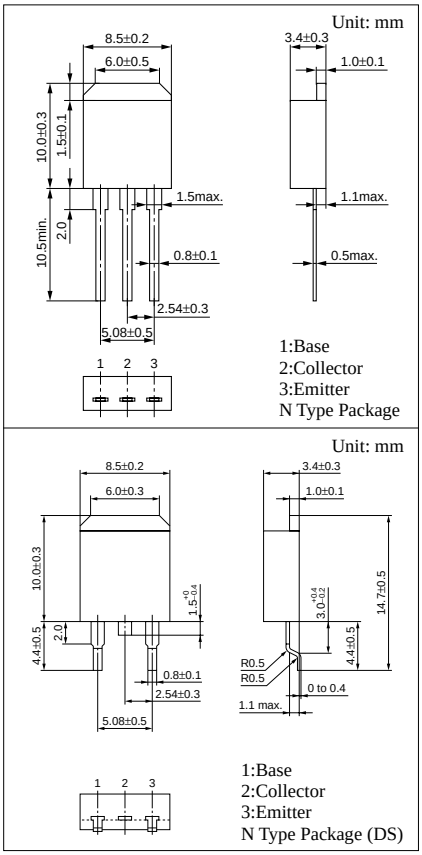
Silicon NPN epitaxial planar type

For power switching

Complementary to 2SB934

Features

- Low collector to emitter saturation voltage $V_{CE(sat)}$
- Satisfactory linearity of foward current transfer ratio h_{FE}
- Large collector current I_C
- N type package enabling direct soldering of the radiating fin to the printed circuit board, etc. of small electronic equipment.



Absolute Maximum Ratings (T_C=25˚C)

Parameter		Symbol	Ratings	Unit
Collector to base voltage	2SD1257	V_{CBO}	130	V
	2SD1257A		150	
Collector to emitter voltage	2SD1257	V_{CEO}	80	V
	2SD1257A		100	
Emitter to base voltage		V_{EBO}	7	V
Peak collector current		I_{CP}	15	A
Collector current		I_C	7	A
Collector power dissipation	T_C=25°C	P_C	40	W
	Ta=25°C		1.3	
Junction temperature		T_j	150	˚C
Storage temperature		T_{stg}	–55 to +150	˚C

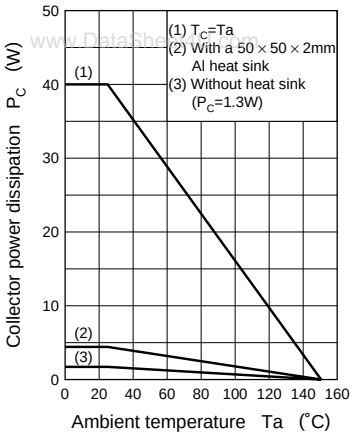
Electrical Characteristics (T_C=25˚C)

Parameter		Symbol	Conditions	min	typ	max	Unit
Collector cutoff current		I_{CBO}	V_{CB} = 100V, I_E = 0			10	µA
Emitter cutoff current		I_{EBO}	V_{EB} = 5V, I_C = 0			50	µA
Collector to emitter voltage	2SD1257	V_{CEO}	I_C = 10mA, I_B = 0	80			V
	2SD1257A			100			
Forward current transfer ratio		h_{FE1}	V_{CE} = 2V, I_C = 0.1A	45			
		h_{FE2}*	V_{CE} = 2V, I_C = 3A	60		260	
Collector to emitter saturation voltage		$V_{CE(sat)}$	I_C = 5A, I_B = 0.25A			0.5	V
Base to emitter saturation voltage		$V_{BE(sat)}$	I_C = 5A, I_B = 0.25A			1.5	V
Transition frequency		f_T	V_{CE} = 10V, I_C = 0.5A, f = 10MHz		30		MHz
Turn-on time		t_{on}	I_C = 3A, I_{B1} = 0.3A, I_{B2} = – 0.3A, V_{CC} = 50V		0.5		µs
Storage time		t_{stg}			1.5		µs
Fall time		t_f			0.1		µs

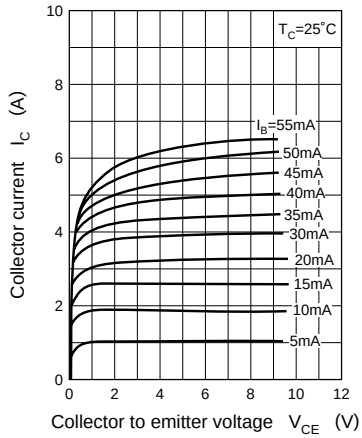
*h_{FE2} Rank classification

Rank	R	Q	P
h_{FE2}	60 to 120	90 to 180	130 to 260

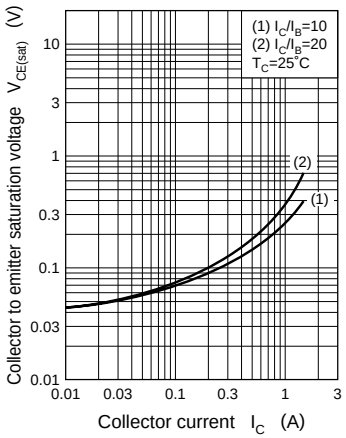
P_C — Ta



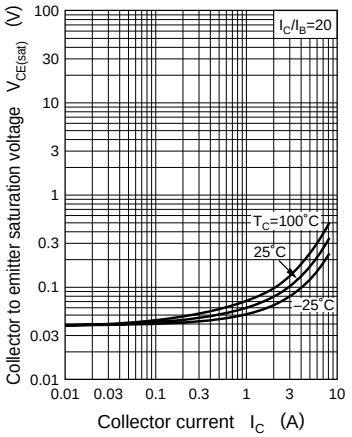
I_C — V_{CE}



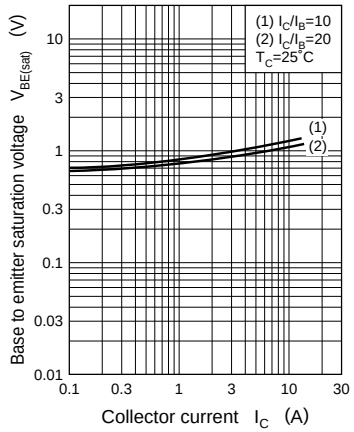
$V_{CE(sat)}$ — I_C



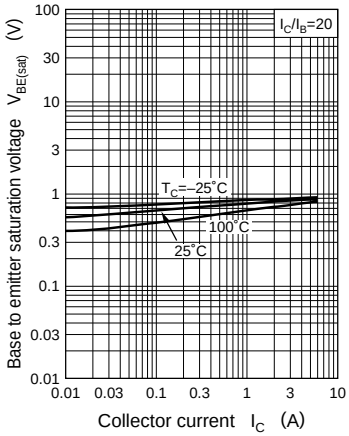
$V_{CE(sat)}$ — I_C



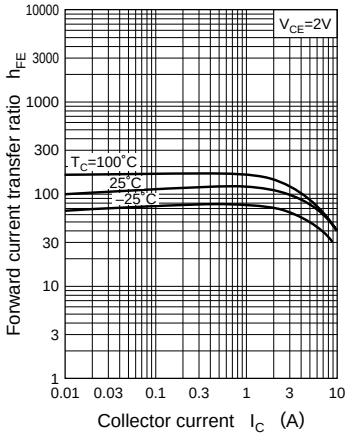
$V_{BE(sat)}$ — I_C



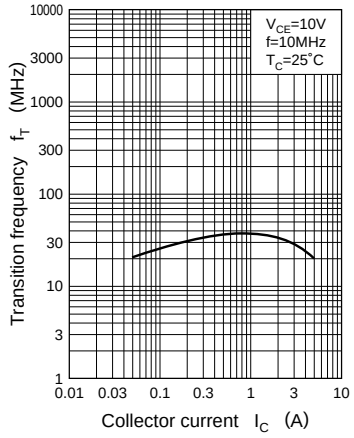
$V_{BE(sat)}$ — I_C



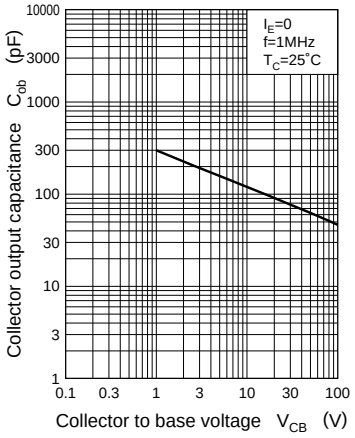
h_{FE} — I_C



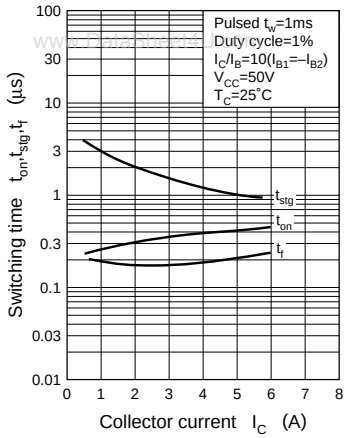
f_T — I_C



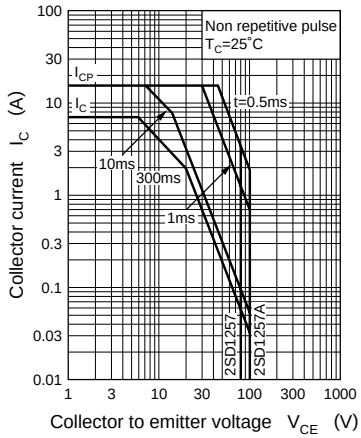
C_{ob} — V_{CB}



t_{on}, t_{stg}, t_f — I_C



Area of safe operation (ASO)



$R_{th(t)}$ — t